CNA1312K

Photo Interrupter

For contactless SW and object detection

■ Overview

CNA1312K is an ultraminiature, highly reliable transmissive photosensor in which a high efficiency GaAs infrared light emitting diode chip and a high sensitivity Si phototransistor chip are integrated in a double molded resin package.

■ Features

- Ultraminiature: 2.6 mm × 4.9 mm (height: 3.3 mm)
- Highly precise position detection: 0.1 mm
- Gap width: 2.0 mm

■ Absolute Maximum Ratings T_a = 25°C

Parameter		Symbol	Rating	Unit
Input (Light emitting diode)	Power dissipation *1	P_D	75	mW
	Forward current	I_F	50	mA
	Reverse voltage	V_R	6	V
Output (Photo transistor)	Collector-emitter voltage (Base open)	V_{CEO}	35	V
	Emitter-collector voltage (Base open)	V_{ECO}	6	V
	Collector current	I_C	20	mA
	Collector power dissipation *2	P_C	75	mW
Operating ambient temperature		T_{opr}	–25 to +85	°C
Storage temperature		T_{stg}	–40 to +100	°C

Note) *1: Input power derating ratio is 1.0 mW/°C at $T_a \geq 25$°C

*2: Output power derating ratio is 1.0 mW/°C at $T_a \geq 25$°C

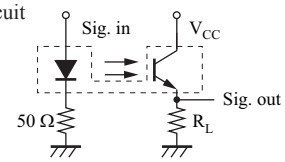
■ Electrical-Optical Characteristics T_a = 25°C±3°C

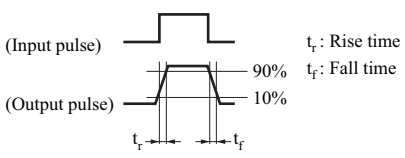
Parameter		Symbol	Conditions	Min	Typ	Max	Unit
Input characteristics	Reverse current	I_R	V_R = 3 V			10	μA
	Forward voltage	V_F	I_F = 20 mA		1.2	1.4	V
Output characteristics	Collector-emitter cutoff current (Base open)	I_{CEO}	V_{CE} = 20 V			100	nA
Transfer characteristics	Collector current	I_C	V_{CE} = 5 V, I_F = 5 mA	40		400	μA
	Collector-emitter saturation voltage	$V_{CE(sat)}$	I_F = 10 mA, I_C = 50 μA			0.4	V
	Rise time *	t_r	V_{CC} = 5 V, I_C = 0.1 mA, R_L = 1 000 Ω		50		μs
	Fall time *	t_f			50		μs

Note) 1. Input and output are practiced by electricity.

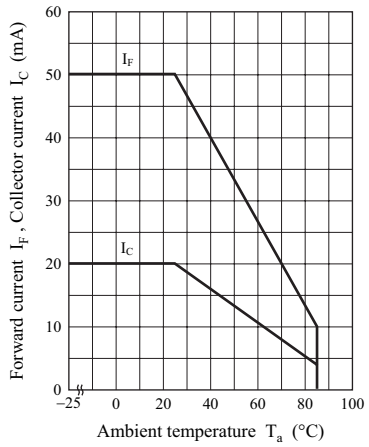
2. This device is designed by disregarding radiation.

3. *: Switching time measurement circuit

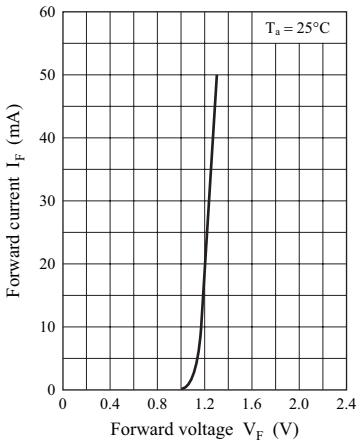




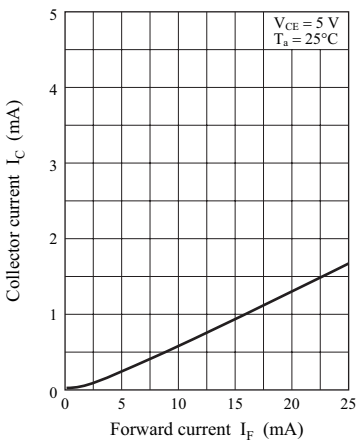
I_F , I_C — T_a



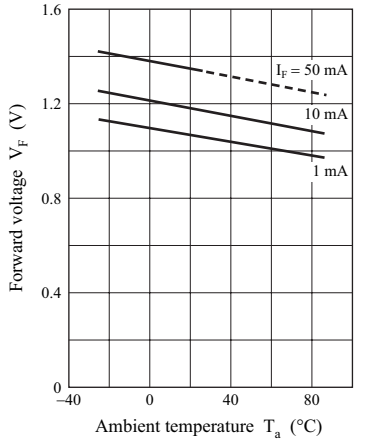
I_F — V_F



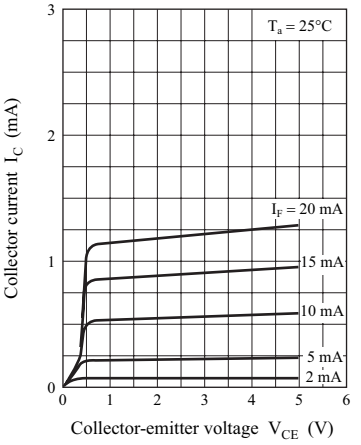
I_C — I_F



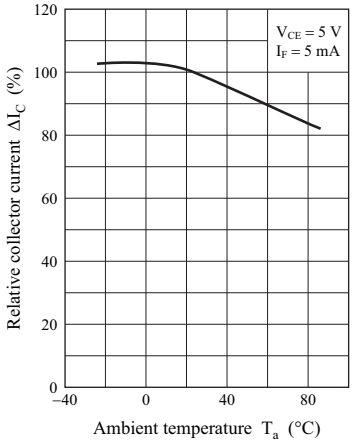
V_F — T_a



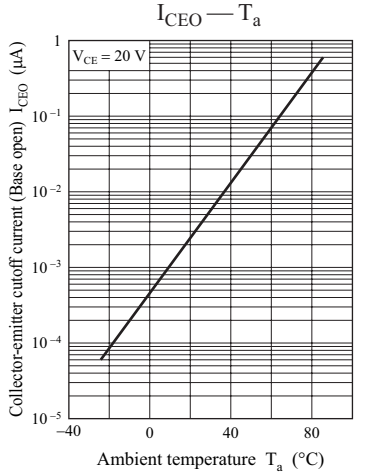
I_C — V_{CE}



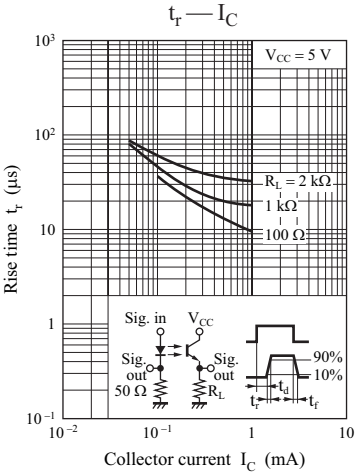
ΔI_C — T_a



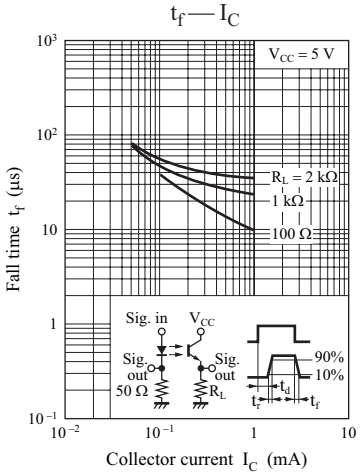
I_{CEO} — T_a



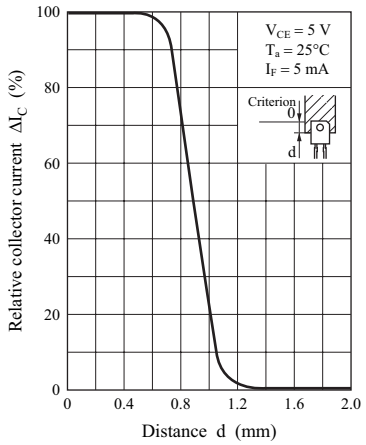
t_r — I_C



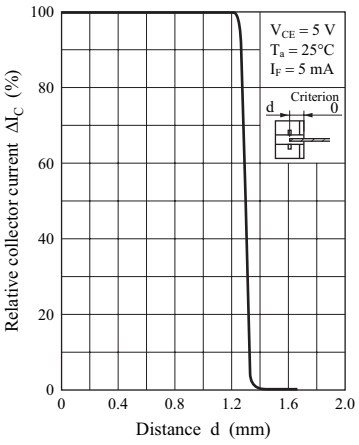
t_f — I_C



ΔI_C — d (1)

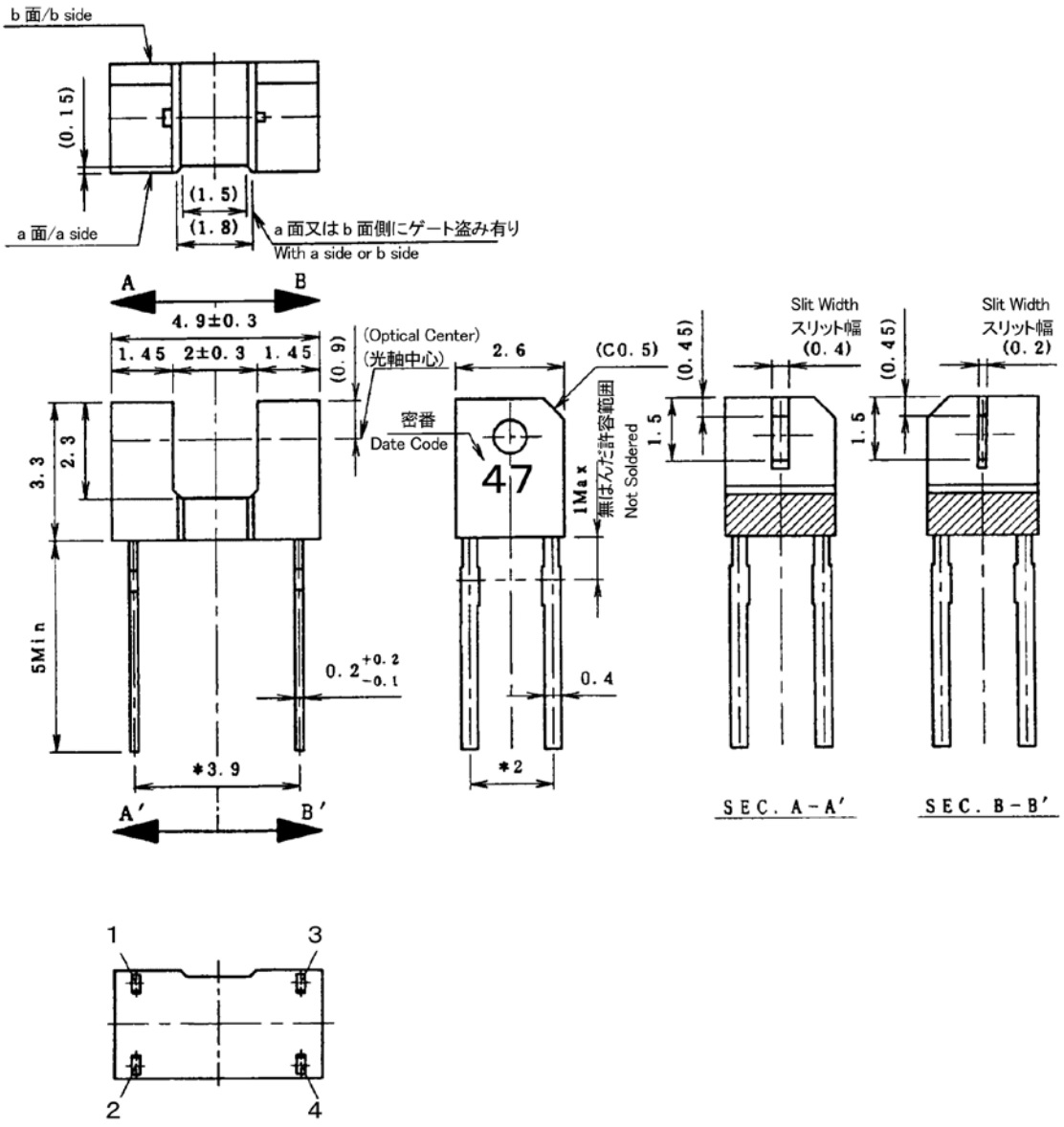


ΔI_C — d (2)



■ Package (Unit: mm)

LSMSIN4S0003



(注 1) ＊リード根元寸法とします。／(Note1)＊Indicates root dimensions of lead.
(注 2) 指示無き寸法公差は±0.2。／(Note2)Not appointment tolerance :±0.2.
(注 3) 密番は、目視又は顕微鏡に於いて解読できる事。
(Note3)What a date code sees an attention and can decode in a microscope.

- Pin name
  1: Anode
  2: Cathode
  3: Collector
  4: Emitter

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